



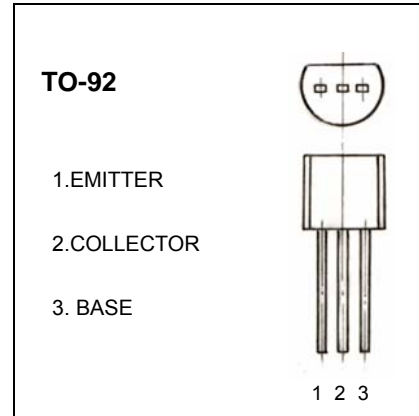
C945 TRANSISTOR (NPN)

FEATURE

- Excellent h_{FE} linearity
- Low noise
- Complementary to A733

MAXIMUM RATINGS ($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	150	mA
P_C	Collector Power Dissipation	400	mW
T_J	Junction Temperature	125	$^{\circ}C$
T_{stg}	Storage Temperature	-55-125	$^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=100uA, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100mA, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=60V, I_E=0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=45V$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=6V, I_C=1mA$	70		700	
	$h_{FE(2)}$	$V_{CE}=6V, I_C=0.1mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100mA, I_B=10mA$			1	V
Transition frequency	f_T	$V_{CE}=6V, I_C=10mA, f=30MHz$	200			MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$			3.0	pF
Noise figure	NF	$V_{CE}=6V, I_C=0.1mA$ $R_G=10k\Omega, f=1kHz$			10	dB

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y	GR	BL
Range	70-140	120-240	200-400	350-700